

SMAF Schottky Barrier Rectifier Diode 肖特基势垒整流二极管
■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMAF


■Maximum Rating 最大额定值

 (T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	SS32F	SS33F	SS34F	SS35F	SS36F	SS38F	SS39F	SS310F	Unit 单位
Peak Reverse Voltage 反向峰值电压	V _{RRM}	20	30	40	50	60	80	90	100	V
DC Reverse Voltage 直流反向电压	V _R	20	30	40	50	60	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	14	21	28	35	42	56	63	70	V
Forward Rectified Current 正向整流电流	I _F	3								A
Peak Surge Current 峰值浪涌电流	I _{FSM}	80								A
Thermal Resistance J-L 结到管脚热阻	R _{θJL}	10								℃/W
Junction Temperature 结温	T _J	150								℃
Storage Temperature 储藏温度	T _{stg}	-65to+150℃								℃

■Electrical Characteristics 电特性

 (T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	SS32F-SS34F	SS35F-SS36F	SS38F-SS310F	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.55	0.70	0.85	V	I _F =3A
Reverse Current 反向电流	I _R (25℃) (100℃)	0.1 5		0.02 2	mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	300			pF	V _R =4V,f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

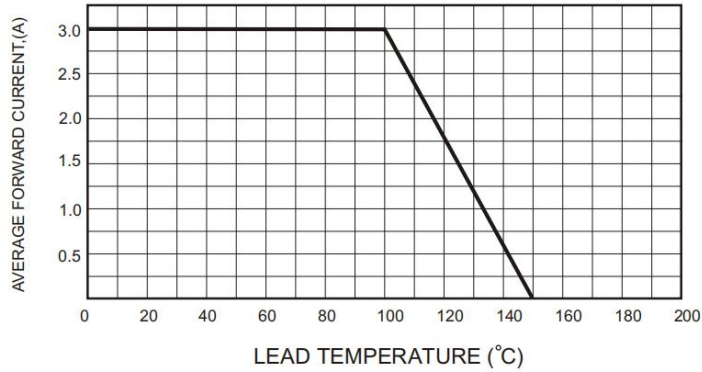


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

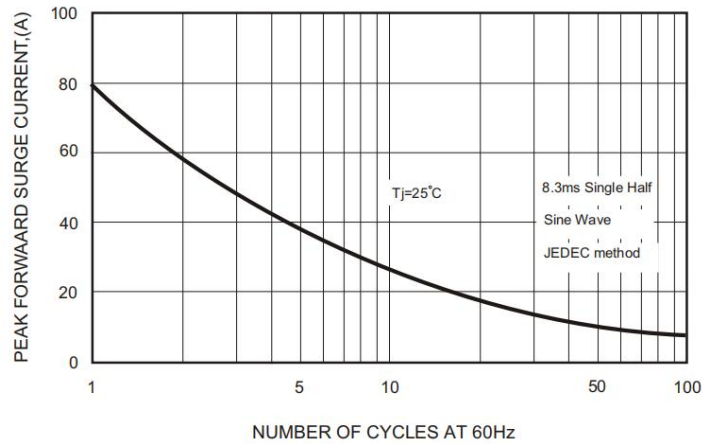


FIG.4-TYPICAL JUNCTION CAPACITANCE

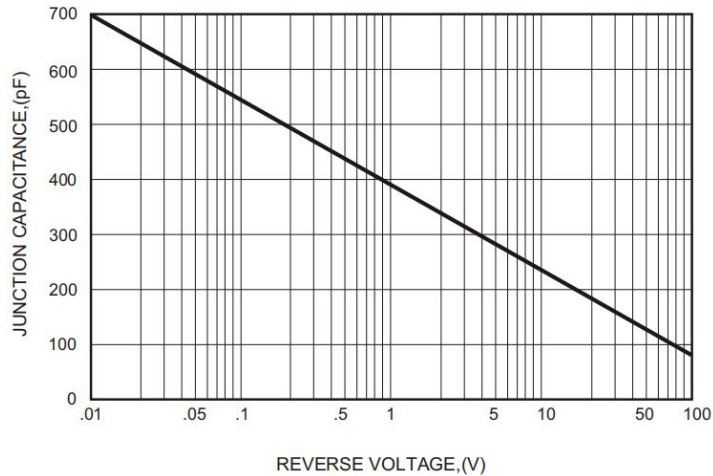


FIG.2-TYPICAL FORWARD

CHARACTERISTICS

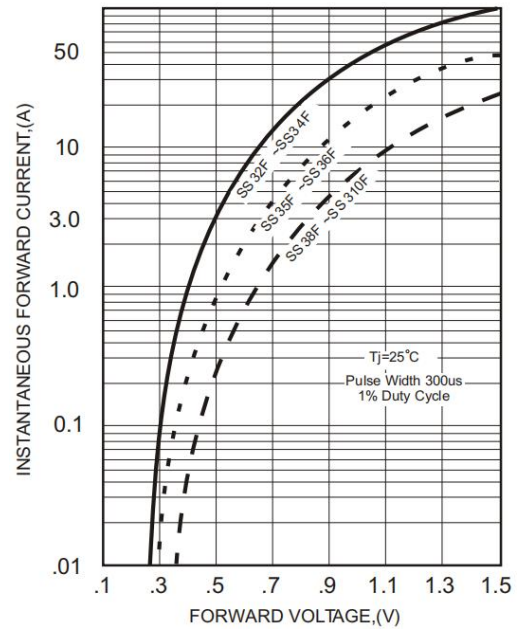
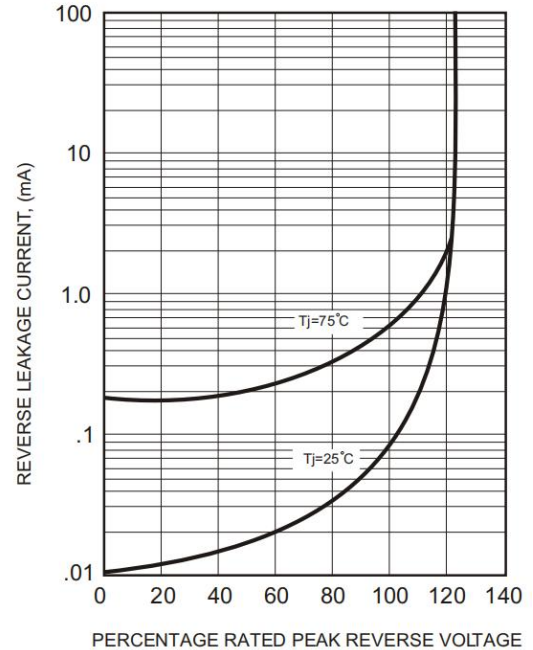
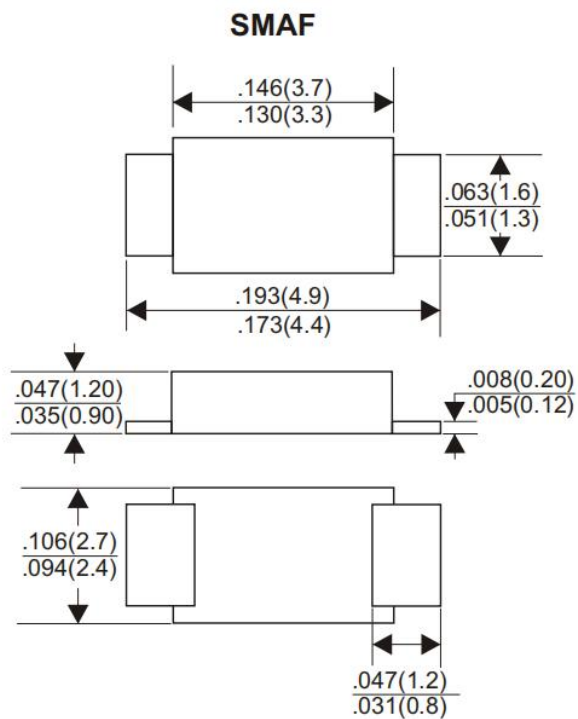


FIG.5 - TYPICAL REVERSE

CHARACTERISTICS



■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)